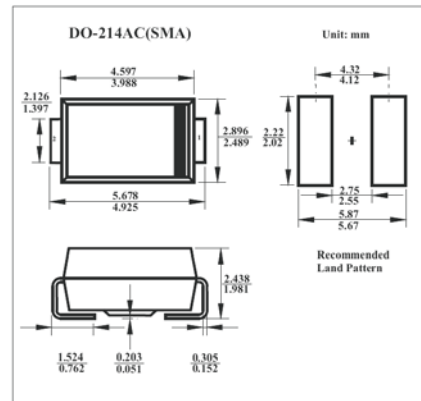


SS22 THRU SS210

■ Features

- For surface mounted applications.
- Low profile package.
- Built-in strain relief.
- Metal silicon junction, majority carrier conduction.
- Low power loss, high efficiency.
- High current capability, low forward voltage drop.
- High surge capability.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	SS22	SS23	SS24	SS25	SS26	SS29	SS210	Unit	
Maximum repetitive peak reverse voltage	VRRM	20	30	40	50	60	90	100	V	
Maximum RMS voltage	VRMS	14	21	28	35	42	63	70	V	
Maximum DC blocking voltage	VDC	20	30	40	50	60	90	100	V	
Maximum average forward rectified current at TL	I(AV)	2							A	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	50							A	
Maximum instantaneous forward voltage at 2.0A * 1	VF	0.5			0.7		0.85		V	
Maximum DC reverse current * 1 TA=25°C at rated DC blocking voltage TA=100°C	IR	0.4					0.1		mA	
		10					20			
Typical thermal resistance	RθJA	55							°C/W	
	RθJL	17								
Operating junction temperature range	TJ	-65 to +125				-65 to +150			°C	
Storage temperature range	Tstg	-65 to +150								°C

* 1. Pulse test: 300 μs pulse width, 1% duty cycle.